

HAT2132H

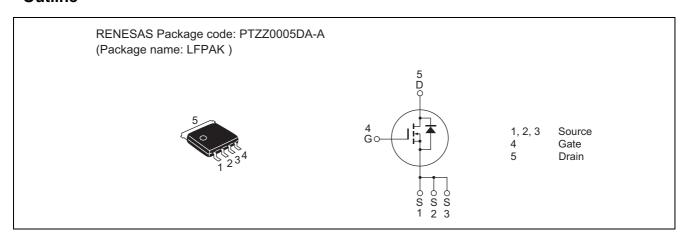
Silicon N Channel MOS FET High Speed Power Switching

REJ03G0177-0300 Rev.3.00 Dec 07, 2006

Features

- Low drive current.
- Low on-resistance
- Low profile

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

Item	Symbol	Ratings	Unit
Drain to source voltage	V _{DSS}	200	V
Gate to source voltage	V _{GSS}	±30	V
Drain current	I _D	6	A
Drain peak current	I _{D(pulse)} Note1	24	A
Body-drain diode reverse drain current	I _{DR}	6	A
Body-drain diode reverse drain peak current	I _{DR(pulse)} Note1	24	A
Avalanche current	I _{AP} Note3	6	A
Avalanche energy	E _{AR} Note3	2.4	mJ
Channel dissipation	Pch Note2	20	W
Channel to case thermal impedance	θch-c	6.25	°C/W
Channel temperature	Tch	150	°C
Storage temperature	Tstg	-55 to +150	°C

Notes: 1. $PW \le 10 \mu s$, duty cycle $\le 1\%$

2. Value at Tc = 25°C

3. STch = 25° C, Tch $\leq 150^{\circ}$ C

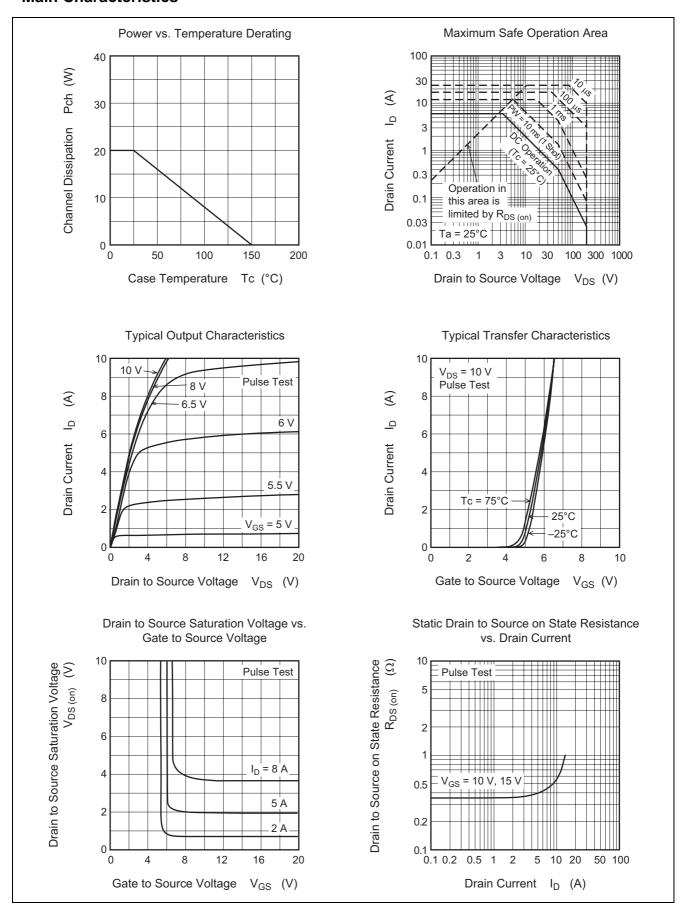
Electrical Characteristics

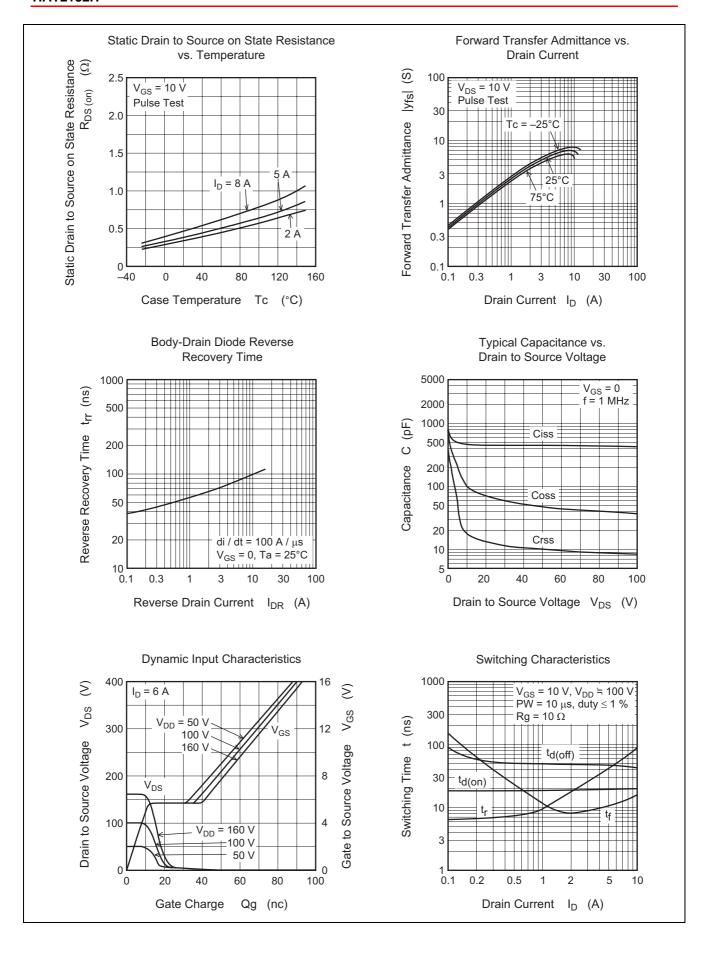
 $(Ta = 25^{\circ}C)$

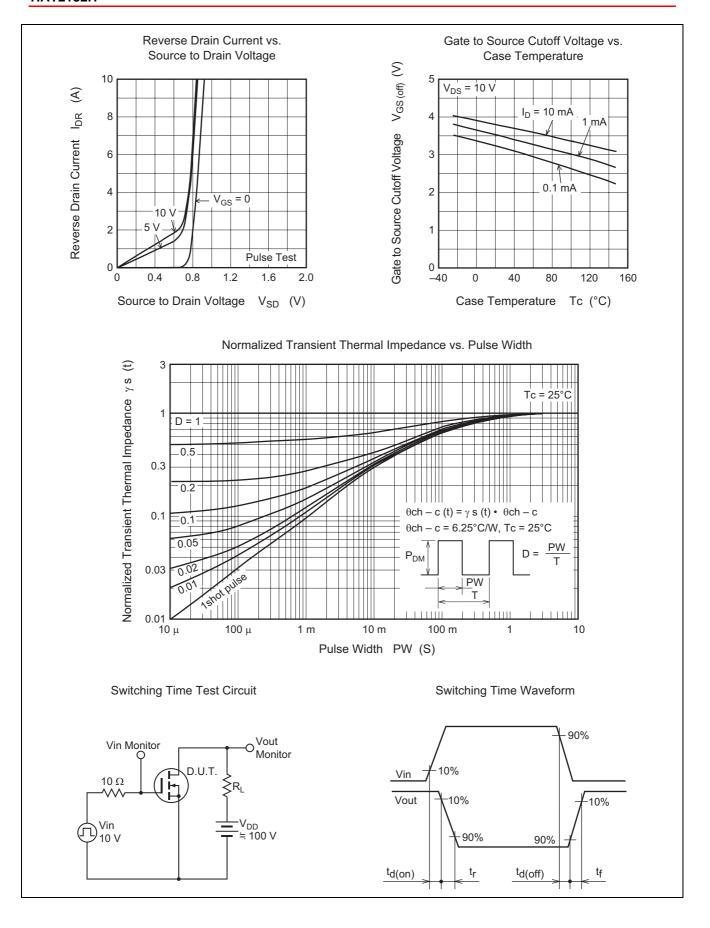
Item	Symbol	Min	Тур	Max	Unit	Test conditions	
Drain to source breakdown voltage	$V_{(BR)DSS}$	200	_	_	V	$I_D = 10 \text{ mA}, V_{GS} = 0$	
Zero gate voltage drain current	I _{DSS}	_	_	1	μΑ	$V_{DS} = 200 \text{ V}, V_{GS} = 0$	
Gate to source leak current	I _{GSS}	_	_	±0.1	μΑ	$V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$	
Gate to source cutoff voltage	$V_{GS(off)}$	3.0	_	4.0	V	$V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$	
Forward transfer admittance	y _{fs}	2.7	4.7	_	S	$I_D = 3 \text{ A}, V_{DS} = 10 \text{ V}^{Note4}$	
Static drain to source on state resistance	R _{DS(on)}	_	0.36	0.45	Ω	$I_D = 3 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$	
Input capacitance	Ciss	_	450	_	pF	V _{DS} = 25 V	
Output capacitance	Coss	_	65	_	pF	$V_{GS} = 0$	
Reverse transfer capacitance	Crss	_	13	_	pF	f = 1 MHz	
Turn-on delay time	t _{d(on)}	_	19	_	ns	I _D = 3 A	
Rise time	t _r	_	26	_	ns	V _{GS} = 10 V	
Turn-off delay time	t _{d(off)}	_	48	_	ns	$R_L = 33.3 \Omega$ $Rg = 10 \Omega$	
Fall time	t _f	_	9	_	ns		
Total gate charge	Qg	_	12.5	_	nC	V _{DD} = 160 V	
Gate to source charge	Qgs	_	2.5	_	nC	V _{GS} = 10 V	
Gate to drain charge	Qgd	_	6	_	nC	$I_D = 6 A$	
Body-drain diode forward voltage	V_{DF}	_	0.85	1.30	V	$I_F = 6 \text{ A}, V_{GS} = 0$ Note4	
Body-drain diode reverse recovery time	t _{rr}	_	95	_	ns	$I_F = 6 \text{ A}, V_{GS} = 0$	
						di _F /dt = 100 A/μs	

Notes: 4. Pulse test

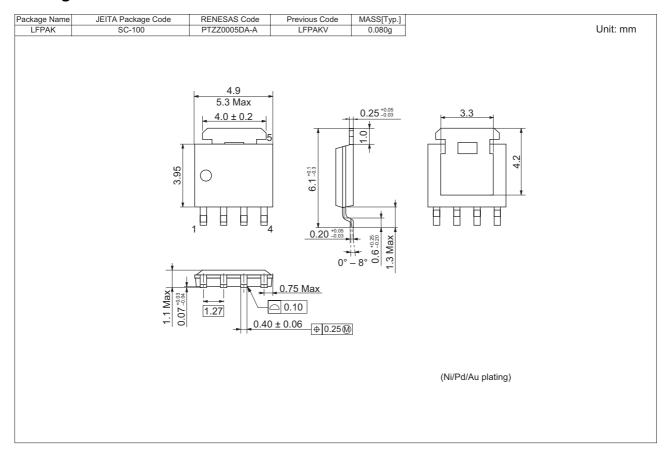
Main Characteristics







Package Dimensions



Ordering Information

Part No.	Quantity	Shipping Container
HAT2132H-EL-E	2500 pcs	Taping

Note: For some grades, production may be terminated. Please contact the Renesas sales office to check the state of production before ordering the product.

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